

### **FEATURES**

- Compliant with LIN 2.0, LIN 2.1, LIN 2.2, LIN 2.2A and SAE J260
- ➤ AEC-Q100 qualified
- Compatible with K line
- ➤ Integrated over-temperature protection function (thermal shutdown)
- ➤ Integrated bus pull-up slave termination resistor
- > Bus current limiting protection
- Supply undervoltage protection
- Very low power consumption sleep mode and standby mode
- Support remote wake-up
- > Support logic input levels with 3.3V and 5V
- ➤ LIN data transmission rate up to 20kbps
- ➤ Low ElectroMagnetic Emissions (EME)
- ➤ Available in SOP8 and DFN3\*3-8 packages

### PRODUCT APPEARANCE



Fig 1. Provide environmentally friendly lead-free package

### DESCRIPTION

SIT1029Q is a local interconnect network (LIN) physical layer transceiver that complies with LIN 2.0, LIN 2.1, LIN 2.2, LIN 2.2A, ISO 17987-4:2016 (12V) and SAE J2602 standards. It is mainly suitable for in-vehicle networks with a transmission rate of 1kbps to 20kbps. SIT1029Q controls the state of the LIN bus through the TXD pin, and can convert the data stream sent by the protocol controller into a bus signal with the best slew rate and waveform shaping to minimize electromagnetic radiation emission (EME). The LIN bus output pin has an internal pull-up resistor. Only when used as a master node, the LIN bus port needs to be pulled up to V<sub>BAT</sub> through an external resistor in series with a diode. SIT1029Q receives the data stream on the bus through the LIN pin, and transmits the data to the external microcontroller through the receiver's output pin RXD.

SIT1029Q can operate from 5.5V to 18V and support 12V applications. SIT1029Q has an extremely low quiescent current consumption in sleep mode and standby mode. It can quickly minimize power consumption in the event of a failure. The device can be placed in normal mode via a signal on the pin SLP N. SIT1029Q supports integrated TXD dominant timeout detection function.



### PIN CONFIGURATION

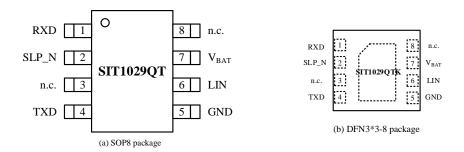


Fig 2. SIT1029Q pin configuration diagrams

## PIN DESCRIPTION

Table 1. SIT1029Q pin description

Pin	Symbol	Description
1	RXD	receive data output (open-drain); active LOW after a wake-up event
2	SLP_N	sleep control input (active LOW); resets wake-up request on RXD
3	n.c.	not connected
4	TXD	transmit data input
5	GND	ground
6	LIN	LIN bus line input/output
7	$V_{BAT}$	battery supply voltage
8	n.c.	not connected

NOTE: In the DFN3\*3-8 package, the pad on the back is connected to the GND pin of the chip. In order to obtain better heat dissipation performance, the pad on the back can be connected to a suitable "ground" on the PCB board.

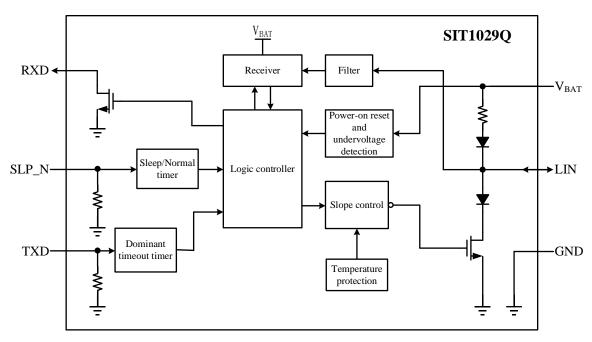


Fig 3. Block diagram

### FEATURE DESCRIPTION

### 1 Overview

The SIT1029Q is an interface device used between the LIN protocol controller and the physical bus. It can be used for in-vehicle and industrial control with a data rate up to 20kBd. The SIT1029Q receives the data stream sent by protocol controller at the pin TXD, and converts it into a bus signal with appropriate slew rate and waveform shaping. The input data on LIN bus is output to external microcontroller by pin RXD. This device is compliant with LIN 2.0, LIN 2.1, LIN 2.2, LIN 2.2A, ISO 17987-4:2016 (12V) and SAE J2602 standards.

#### 2 Short-circuit protection

Pin TXD provides an internal pull-down to GND to apply a predefined level on TXD when it is not enabled. The pin SLP\_N also provides an internal pull-down to force the transceiver to enter sleep mode when SLP\_N is not enabled.

Pin RXD will be left floating and limit the output current of transmitter to prevent a short-circuit between transmitter and  $V_{BAT}$  or GND if the supply on pin  $V_{BAT}$  is turned off. The power outage (pin  $V_{BAT}$  and GND) has no effect on the bus and microcontroller. The bus has no reverse current, and the LIN transceiver can be disconnected from the power supply without affecting the LIN bus.



#### 3 Thermal Shutdown

In normal mode, the over-temperature protection circuit will disable the output driver when the junction temperature of SIT1029Q exceeds the shutdown junction temperature  $T_{j(sd)}$ . When the junction temperature is lower than the hysteresis temperature, the driver is enabled again.

### 4 Undervoltage detection on VBAT

If  $V_{BAT}$  is lower than  $V_{th(VBATL)L}$  during use, the protection circuit will disable the output driver. When  $V_{BAT}$ >  $V_{th(VBATL)H}$ , the driver will be enabled again.

### **5 Operating modes**

As shown in Fig 4, the SIT1029Q supports four functional modes for very-low-power operation (Sleep mode), standby operation (Standby mode), normal operation (Normal mode) and power-up (Power-on mode). The operating states in each mode are shown in Table 2.

**Sleep mode:** This mode is the most power saving mode of the SIT1029Q. It can be woken up remotely via pin LIN, or activated directly via pin SLP\_N. In order to prevent SIT1029Q from waking up due to accidental wake-up events caused by automotive transients or EMI, filters are designed at the receiver's input (LIN pin) and SLP\_N pin. The necessary condition for SIT1029Q to be awakened in sleep mode is: the time to wake it up remotely through the LIN pin must be greater than t<sub>wake(dom)LIN</sub> (the wake-up time of LIN); the time to wake up directly through the SLP N pin must be greater than t<sub>gotonorm</sub>.

In normal mode, when SLP\_N pin has a falling edge and SLP\_N remains low for longer than t<sub>gotosleep</sub>, SIT1029Q enters sleep mode.

**Standby mode:** SIT1029Q has very low static power consumption in this mode. When SIT1029Q is in sleep mode, if a remote wake-up event is detected, the device will automatically enter standby mode immediately, and the low level on the RXD pin will indicate that the wake-up process is used to send an interrupt flag to the MCU.

Setting pin SLP N high during Standby mode may result in the following events:

- (1) A change into Normal mode if the high level on pin SLP\_N has been maintained for a certain time period (tgotonorm).
- (2) An immediate reset of the wake-up request signal on pin RXD.

**Normal mode:** Only in Normal mode, the receiver and transmitter are active and the SIT1029Q is able to transmit and receive data via the LIN bus. The high level of bus represents recessive and low level represents dominant. The receiver detects the data stream on the LIN bus and outputs it to the microcontroller via pin RXD. Normal mode is entered as a high level on pin SLP\_N and maintained for a time of at least t<sub>gotonorm</sub> while the SIT1029Q is in Sleep or Standby mode. The Sleep mode is entered by setting pin SLP\_N low for longer than t<sub>gotosleep</sub>.



**Power-on mode:** If the voltage on  $V_{BAT}$  is less than the low-level reset threshold  $V_{th(VBATL)L}$  when powering on, the SIT1029Q is in power-on reset mode and all input and output functions are disabled; when the voltage on  $V_{BAT}$  is greater than the high-level reset threshold  $V_{th(VBAT)H}$ , SIT1029Q enters sleep mode.

#### 6 Wake Up Events

In sleep mode, the device can be awakened by the following two ways:

- (1) Remote wake-up via pin LIN;
- (2) Wake up directly via mode transition. If SLP\_N is held HIGH for t<sub>gotonorm</sub>, the device will switch from sleep mode to normal mode.

#### 7 Remote Wake Up Events

LIN pin remote wake-up: When the LIN pin is pulled down to a low level through a falling edge, a rising edge appears at the next moment, and the low-level holds time between the rising edge and the falling edge at the previous moment is greater than  $t_{wake(dom)LIN}$ , the process is regarded as effective remote wake-up (as shown in Fig 5).

After the remote wake-up, the wake-up request event interrupts the microcontroller with the low level of the RXD pin as the indicator signal.

#### **8 Dominant Timeout Function**

If the TXD pin is forced to be permanently low due to hardware and/or software application failures, the integrated TXD dominant timeout timer circuit prevents the bus line from being driven to a permanently dominant state (blocking all network communications). The timer is triggered by the falling edge on the TXD pin. If the low level on the TXD pin holds longer than the internal timer time ( $t_{to(dom)TXD}$ ), the transmitter will be disabled and the drive bus will go into a recessive state. The timer is reset by the rising edge on the TXD pin.

#### 9 Failure Safety Feature

- > The interior of the TXD pin is pulled down to the ground to prevent the undefined floating state of the TXD pin.
- The interior of the SLP\_N pin is pulled down to the ground, and the corresponding LIN transceiver will enter the sleep mode when the SLP N pin is floating.
- > The ground loss condition has no effect on the bus port, and the bus port has no reverse current.
- $\triangleright$  The bus driver output stage current limiting to prevent the driver from burning down or functional effects when the bus short-circuits to the  $V_{BAT}$ .
- > To avoid the effects caused by TXD pins being forced to permanently low due to hardware and/or



software application failures, after switching to normal mode, the LIN driver will be enabled only if a high TXD level is detected.

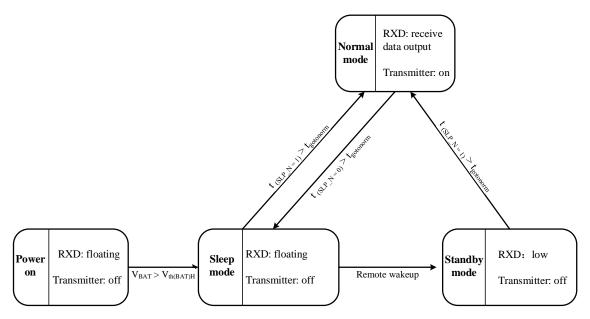


Fig 4. State diagram

Table 2. Working status of SIT1029Q in each mode

Mode	SLP_N	RXD	Transmitter	Remarks
Sleep	low	floating	off	no wake-up request detected
Standby	low	low	off	wake-up request detected
Normal	high	recessive: high dominant: low	on	Enable bus signal shaping
Power-on	low	floating	off	Disable all input and output functions

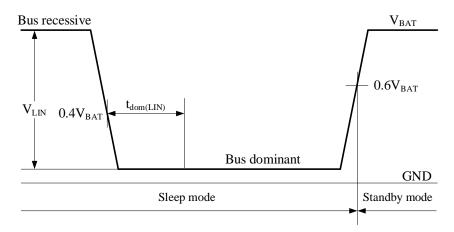


Fig 5. Remote wake-up behavior



## LIMITING VALUES

Parameter	Parameter Symbol Conditions		Range	Unit
battery supply voltage	$V_{\mathrm{BAT}}$	with respect to GND	-0.3 ~ +42	V
1 TVD	37	ISLP_N no limitation	<b>-0.3</b> ∼ +6	V
voltage on pin TXD	$V_{TXD}$	I <sub>SLP_N</sub> < 500μA	<b>-0.3</b> ∼ +7	V
14	3.7	ISLP_N no limitation	<b>-</b> 0.3 ∼ +6	V
voltage on pin RXD	$V_{RXD}$	$I_{SLP\_N} < 500 \mu A$	<b>-0.3</b> ∼ +7	V
t ' CLD N	17	ISLP_N no limitation	<b>-</b> 0.3 ∼ +6	17
voltage on pin SLP_N	$ m V_{SLP\_N}$	$I_{SLP\_N} < 500 \mu A$	<b>-0.3</b> ∼ +7	V
voltage on pin LIN	$V_{ m LIN}$	with respect to GND	-42 ~ +42	V
virtual junction temperature	$T_{\rm j}$		-40 ~ 150	°C
storage temperature	$T_{stg}$		-55 ∼ 150	°C
ambient temperature	$T_{amb}$		-40 ~ 125	°C
ESD, human body		On pins LIN and VBAT	<b>-8</b> ∼ <b>+8</b>	kV
model		On pins RXD, SLP_N and TXD	<b>-</b> 2 ∼ +2	kV
ESD, charge device model	$ m V_{ESD}$	All pins	-750 ∼ +750	V
ESD, machine model		All pins	-200 ~ +200	V
ESD, IEC61000-4-2		On pins LIN and VBAT	-4 ~ +4	kV

The maximum limit parameters mean that exceeding these values may cause irreversible damage to the device. Under these conditions, it is not conducive to the normal operation of the device. The continuous operation of the device at the maximum allowable rating may affect the reliability of the device. The reference point for all voltages is ground.



# STATIC CHARACTERISTICS

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Supply						
battery supply voltage	$ m V_{BAT}$		5.5	12	18	V
Power consumption	1					
		Sleep mode bus recessive $(V_{LIN}=V_{BAT}; V_{SLP\_N}=0V)$	1	4	10	μΑ
		Sleep mode bus dominant $(V_{LIN}=V_{BAT}; V_{SLP\_N}=0V)$	100	350	1000	μΑ
	I <sub>BAT</sub>	Standby mode bus recessive $(V_{LIN}=V_{BAT}; V_{SLP\_N}=0V)$	1	4	10	μА
battery supply current		Standby mode bus dominant (V <sub>BAT</sub> =12V; V <sub>LIN</sub> =0V; V <sub>SLP N</sub> =0V)	100	350	1000	μΑ
		Normal mode bus recessive (V <sub>LIN</sub> =V <sub>BAT</sub> ; V <sub>TXD</sub> =5V; V <sub>SLP_N</sub> =5V)	50	160	300	μΑ
		Normal mode bus dominant ( $V_{BAT}$ =12V; $V_{TXD}$ =0V; $V_{SLP_N}$ =5V)	0.5	1.6	3	mA
Power-on reset						
LOW-level V <sub>BAT</sub> reset threshold voltage	$V_{\text{th(VBATL)L}}$		3.9	4.4	4.7	V
HIGH-level V <sub>BAT</sub> reset threshold voltage	$V_{\text{th(VBATL)H}}$		4.2	4.7	5.1	V



Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
V <sub>BAT</sub> reset	V <sub>hys(VBATL)</sub> <sup>[1]</sup>		0.15	0.3	0.6	V
hysteresis voltage	v hys(VBAIL)		0.13	0.5	0.0	v
Pin TXD						
HIGH-level input	$ m V_{IH}$		2		7	V
voltage	V IH			_	,	· ·
LOW-level input	$ m V_{IL}$		-0.3	_	0.8	V
voltage					0.0	
hysteresis voltage	$V_{hys}$ <sup>[1]</sup>		50	200	400	mV
pull-down						
resistance on pin	$R_{PD(TXD)}$	$V_{TXD}=5V$	50	125	400	kΩ
TXD						
Pin SLP_N						
HIGH-level input	$ m V_{IH}$		2	_	7	V
voltage	· in				,	•
LOW-level input	$ m V_{IL}$		-0.3	_	0.8	V
voltage						
hysteresis voltage	$V_{hys}$ <sup>[1]</sup>		50	200	400	mV
pull-down						
resistance on pin	$R_{PD(SLP\_N)}$	$V_{SLP\_N}=5V$	100	250	650	kΩ
SLP_N						
Pin RXD						_
LOW-level output		Normal mode;				
current	$I_{\mathrm{OL}}$	$V_{RXD}=0.4V;$	2	-	-	mA
Carrent		V <sub>LIN</sub> =0V				
HIGH-level		Normal mode;	-5	-		
leakage current	$I_{LH}$	$V_{RXD}=5V;$			5	μΑ
		$V_{LIN}=V_{BAT}$				
Pin LIN	Т			1	T	
current limitation		$V_{TXD}=0V;$				
for driver	$I_{BUS\_LIM}$	$V_{LIN}=V_{BAT}=18V$	40	-	100	mA
dominant state						
receiver recessive	T	$V_{TXD}=5V;$			10	
input leakage	I <sub>BUS_PAS_rec</sub>	V <sub>LIN</sub> =18V;	-	-	10	μA
current receiver dominant		V <sub>BAT</sub> =5.5V Normal mode;				
input leakage	Inua rea	V <sub>TXD</sub> =5V; V <sub>LIN</sub> =0V;	-600			μΑ
current	$I_{BUS\_PAS\_dom}$	$V_{TXD}=3V$ , $V_{LIN}=0V$ , $V_{BAT}=12V$	-000	_	-	μΑ
loss-of-ground bus						
current	$I_{BUS\_NO\_GND}$	$V_{BAT}=18V; V_{LIN}=0V$	-1000	-	10	μΑ
	<u> </u>	L		<u> </u>	<u> </u>	<u> </u>



Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
loss-of-battery bus current	I BUS_NO_BAT	$V_{BAT}=0V; V_{LIN}=18V$	-	-	10	μΑ
receiver dominant input voltage	$V_{\text{th(dom)RX}}$		-	-	$0.4 { m V}_{ m BAT}$	V
receiver recessive input voltage	$V_{\text{th(rec)RX}}$		$0.6 { m V}_{ m BAT}$	-	-	V
receiver center voltage	$V_{\text{th(RX)cntr}}$	$V_{\text{th(RX) cntr}} = \\ (V_{\text{th(rec)RX}} + \\ V_{\text{th(dom)RX}})/2$	0.475V <sub>BAT</sub>	$0.5 { m V}_{ m BAT}$	0.525V <sub>BAT</sub>	V
receiver hysteresis threshold voltage	$V_{\text{th(hys)RX}}$	$\begin{array}{c} V_{th(hys)RX} = \\ V_{th(rec)RX} - V_{th(dom)RX} \end{array}$	-	1	$0.175V_{BAT}$	V
slave resistance	$R_{ m slave}$	connected between pins LIN and $V_{BAT}$ ; $V_{LIN}$ =0V; $V_{BAT}$ =12V; $V_{TXD}$ = $V_{SLP}$ _N=5V	20	30	60	kΩ
capacitance on pin LIN	C <sub>LIN</sub> [1]		-	-	20	pF
4		Normal mode; V <sub>TXD</sub> =0V; V <sub>BAT</sub> =7V	-	-	1.4	V
dominant output voltage	$V_{o(\text{dom})}$	Normal mode; $V_{TXD}$ =0V; $V_{BAT}$ =18V	-	-	2.0	V
Thermal shutdown						
shutdown junction temperature	$T_{j(sd)}^{[1]}$		150	-	200	°C

(Unless specified otherwise;  $5.5\text{V} \le \text{V}_{\text{BAT}} \le 18\text{V}$ ,  $-40^{\circ}\text{C} \le \text{T}_{j} \le 150^{\circ}\text{C}$ ; typical in  $\text{V}_{\text{BAT}} = 12\text{V}$ ,  $\text{T}_{\text{amb}} = 25^{\circ}\text{C}$ .)

<sup>[1]</sup> Not tested in production; guaranteed by design.



# SWITCH CHARACTERISTICS

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Duty cycles						•
duty avala 1	δ <u>1</u> [1][2]	$\begin{split} &V_{th(rec)(max)}\!\!=\!\!0.744\!\times\!V_{BAT};\\ &V_{th(dom)(max)}\!\!=\!\!0.581\!\times\!V_{BAT};\\ &t_{bit}\!\!=\!\!50\mu s;\\ &V_{BAT}\!\!=\!\!7V\sim18V,\underline{Fig~6} \end{split}$	0.396	-	-	
duty cycle 1	01 ( );	$\begin{split} &V_{th(rec)(max)}\!\!=\!\!0.76\!\times\!V_{BAT};\\ &V_{th(dom)(max)}\!\!=\!\!0.593\!\times\!V_{BAT};\\ &t_{bit}\!\!=\!\!50\mu s;\\ &V_{BAT}\!\!=\!\!5.5V\sim7V,\underline{Fig~6} \end{split}$	0.396	1	-	
	82 [2][3]	$\begin{split} &V_{th(rec)(min)}{=}0.422{\times}V_{BAT};\\ &V_{th(dom)(min)}{=}0.284{\times}V_{BAT};\\ &t_{bit}{=}50\mu s;\\ &V_{BAT}{=}7.6V\sim18V,\underline{Fig~6} \end{split}$	-	-	0.581	
duty cycle 2	07 (5115)	$\begin{split} &V_{th(rec)(min)}{=}0.41{\times}V_{BAT};\\ &V_{th(dom)(min)}{=}0.275{\times}V_{BAT};\\ &t_{bit}{=}50\mu s;\\ &V_{BAT}{=}6.1V\sim7.6V,\underline{Fig~6} \end{split}$	-	-	0.581	
	83 [1][2]	$\begin{split} &V_{th(rec)(max)}\!\!=\!\!0.778\!\times\!V_{BAT};\\ &V_{th(dom)(max)}\!\!=\!\!0.616\!\times\!V_{BAT};\\ &t_{bit}\!\!=\!\!96\mu s;\\ &V_{BAT}\!\!=\!\!7V\sim18V,\underline{Fig~6} \end{split}$	0.417	-	-	
duty cycle 3		$\begin{split} &V_{th(rec)(max)}\!\!=\!\!0.797\!\times\!V_{BAT};\\ &V_{th(dom)(max)}\!\!=\!\!0.630\!\times\!V_{BAT};\\ &t_{bit}\!\!=\!\!96\mu s;\\ &V_{BAT}\!\!=\!\!5.5V\sim7V,\underline{Fig~6} \end{split}$	0.417	-	-	
duty cycle 4	δ4 [2][3]	$\begin{split} &V_{th(rec)(min)}{=}0.389{\times}V_{BAT};\\ &V_{th(dom)(min)}{=}0.251{\times}V_{BAT};\\ &t_{bit}{=}96\mu s;\\ &V_{BAT}{=}7.6V\sim18V,\underline{Fig~6} \end{split}$	-	-	0.590	
		$\begin{split} &V_{th(rec)(min)}{=}0.378{\times}V_{BAT};\\ &V_{th(dom)(min)}{=}0.242{\times}V_{BAT};\\ &t_{bit}{=}96\mu s;\\ &V_{BAT}{=}6.1V\sim7.6V,\underline{Fig.6} \end{split}$	-	-	0.590	
Timing characteristic	es					
receiver propagation delay	t <sub>PD(RX)</sub> [4]		-	-	6	μs
receiver propagation delay symmetry	t <sub>PD(RX)sym</sub> <sup>[4]</sup>		-2	-	2	μs



Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
LIN dominant wake-up time	$t_{ m wake(dom)LIN}$	Sleep mode	30	80	150	μs
go to normal time	$t_{ m gotonorm}$		2	6	10	μs
go to sleep time	$t_{ m gotosleep}$		2	6	10	μs
Dominant time-out time	$T_{\text{to(dom)TXD}}$		6	12	50	ms

(Unless specified otherwise;  $5.5V \le V_{BAT} \le 18V$ ,  $-40^{\circ}C \le T_{j} \le 150^{\circ}C$ ; typical in  $V_{BAT} = 12V$ ,  $T_{amb} = 25^{\circ}C$ .)

[1] 
$$\delta 1, \delta 3 = \frac{t_{bus(rec)(min)}}{2 \times t_{bit}};$$

[2] Bus load condition: (1)  $C_L$ =1nF,  $R_L$ =1k $\Omega$ ; (2)  $C_L$ =6.8nF,  $R_L$ =660 $\Omega$ ; (3)  $C_L$ =10nF,  $R_L$ =500 $\Omega$ ;

[3] 
$$\delta 2, \delta 4 = \frac{t_{bus(rec)(max)}}{2 \times t_{bit}}$$
;

[4] Load condition pin RXD:  $C_{RXD}$ =20pF,  $R_{RXD}$ =2.4k $\Omega$ .



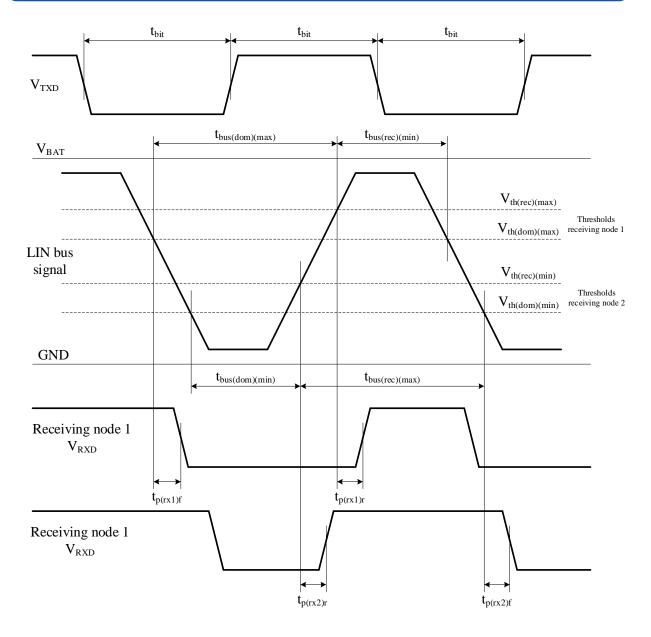


Fig 6. Bus signal transmission timing diagram



## TYPICAL APPLICATION

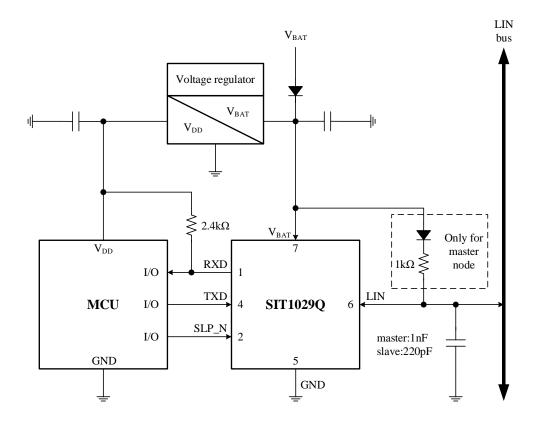


Fig 7. Typical application of the SIT1029Q

# TIMING TEST CIRCUIT

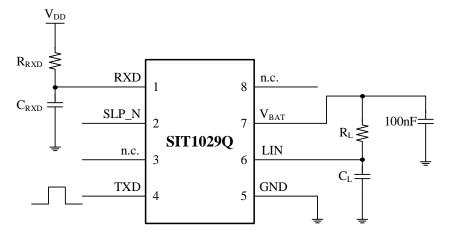


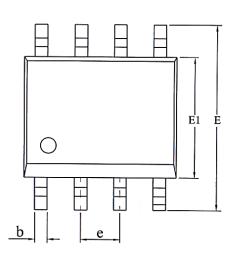
Fig 8. Timing test circuit

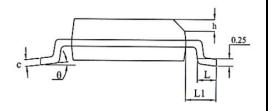


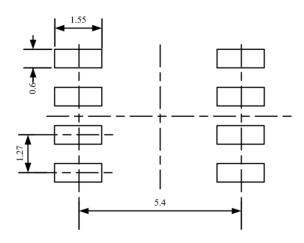
# **SOP8 DIMENSIONS**

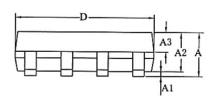
### PACKAGE SIZE

TACKAGE SIZE						
SYMBOL	MIN./mm	TYP./mm	MAX./mm			
A	1.40	-	1.80			
A1	0.10	-	0.25			
A2	1.30	1.40	1.50			
A3	0.60	0.65	0.70			
b	0.38	-	0.51			
D	4.80	4.90	5.00			
Е	5.80	6.00	6.20			
E1	3.80	3.90	4.00			
e		1.27BSC				
L	0.40	0.60	0.80			
L1	1.05REF					
С	0.20	-	0.25			
θ	0°	-	8°			









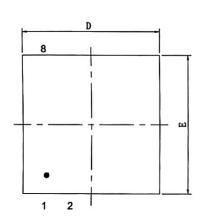
LAND PATTERN EXAMPLE (Unit: mm)

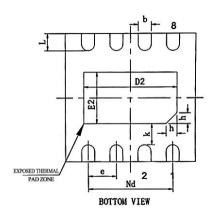


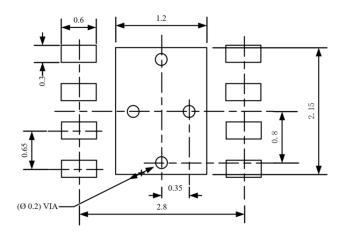
## **DFN3\*3-8 DIMENSIONS**

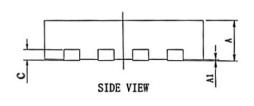
### PACKAGE SIZE

TACKAGE SIZE							
SYMBOL	MIN/mm	TYP/mm	MAX/mm				
A	0.70	0.75	0.80				
A1	0	0.02	0.05				
A3		0.203 REF					
D	2.90	3.00	3.10				
Е	2.90	3.00	3.10				
D2	2.05	2.25					
Nd		1.95BSC					
E2	1.10	1.20	1.30				
b	0.25	0.30	0.35				
e		0.65 TYP					
k	0.50REF						
L	0.35	0.4	0.45				
h	0.20	0.25	0.30				





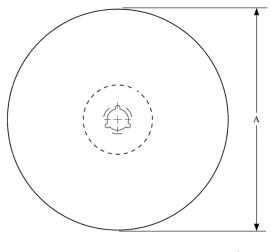




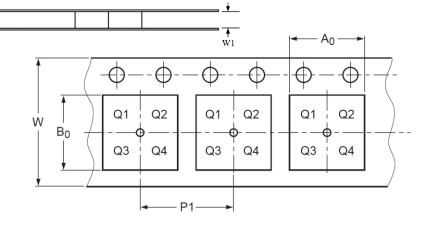
LAND PATTERN EXAMPLE (Unit: mm)



### TAPE AND REEL INFORMATION



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers





Direction of Feed

PIN1 is in quadrant 1

Package type	Reel diameter A (mm)	Tape width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)
SOP8	330±1	12.4	6.60±0.1	5.30±0.10	1.90±0.1	8.00±0.1	12.00±0.1
DFN3*3-8	329±1	12.4	3.30±0.1	3.30±0.1	1.10±0.1	8.00±0.1	12.00±0.3

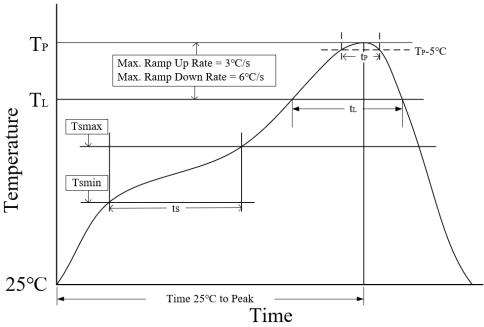
### **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE	PACKING
SIT1029QT	SOP8	Tape and reel
SIT1029QTK	DFN3*3-8, small outline package, no leads	Tape and reel

SOP8 is packed with 2500 pieces/disc in braided packaging, with small outline package and 6000 pieces/disc in lead free packaging.



## REFLOW SOLDERING



Parameter	Lead-free soldering conditions	
Ave ramp up rate (T <sub>L</sub> to T <sub>P</sub> )	3 °C/second max	
Preheat time ts	60-120 seconds	
$(T_{smin}=150 \text{ °C to } T_{smax}=200 \text{ °C})$		
Melting time t <sub>L</sub> (T <sub>L</sub> =217 °C)	60-150 seconds	
Peak temp T <sub>P</sub>	260-265 °C	
5°C below peak temperature t <sub>P</sub>	30 seconds	
Ave cooling rate (T <sub>P</sub> to T <sub>L</sub> )	6 °C/second max	
Normal temperature 25°C to peak temperature	8 minutes max	
TP time		

### Important statement

SIT reserves the right to change the above-mentioned information without prior notice.



# REVISION HISTORY

Version number	Data sheet status	Revision date
V1.0	Initial version.	September 2022
V1.1	Added ambient temperature T <sub>amb;</sub> Updated package dimension schematic (size unchanged).	March 2023
V1.2	Added "AEC-Q100 qualified"; Added ESD related information.	September 2023